

Silicon PNP Power Transistors

2SA738

DESCRIPTION

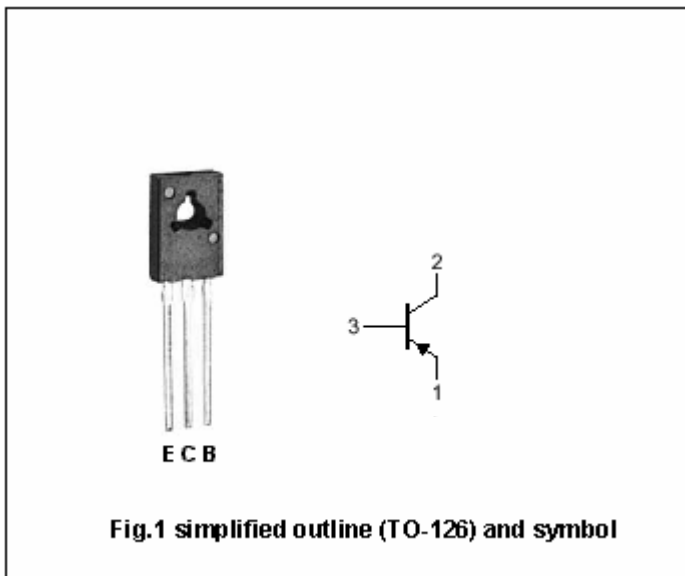
- With TO-126 package
- High current
- Complement to type 2SC1368

APPLICATIONS

- Driver stages in high-fidelity amplifiers and television circuits

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-25	V
V _{CEO}	Collector-emitter voltage	Open base	-25	V
V _{EBO}	Emitter -base voltage	Open collector	-5	V
I _C	Collector current		-1.5	A
I _{CM}	Collector current-Peak		-2.0	A
P _t	Total power dissipation	T _C =25°C	8	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA; I _B =0	-25			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-0.5A; I _B =-50mA			-0.5	V
V _{BE}	Base-emitter voltage	I _C =-500mA ; V _{CE} =-2V			-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-25V; I _E =0			-1.0	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-1.0	μA
h _{FE-1}	DC current gain	I _C =-150mA ; V _{CE} =-2V	35		320	
h _{FE-2}	DC current gain	I _C =-500mA ; V _{CE} =-2V	25			
f _T	Transition frequency	I _C =-50mA; V _{CE} =-5V		160		MHz

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PACKAGE OUTLINE

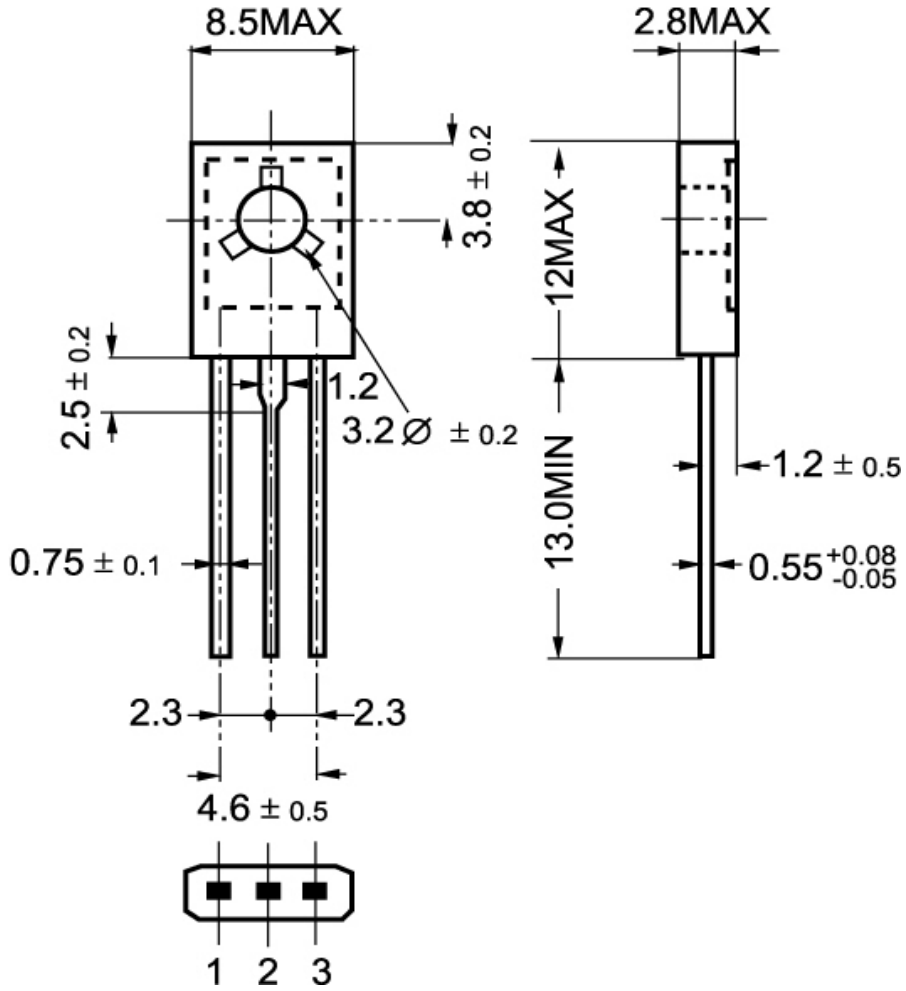


Fig.2 Outline dimensions